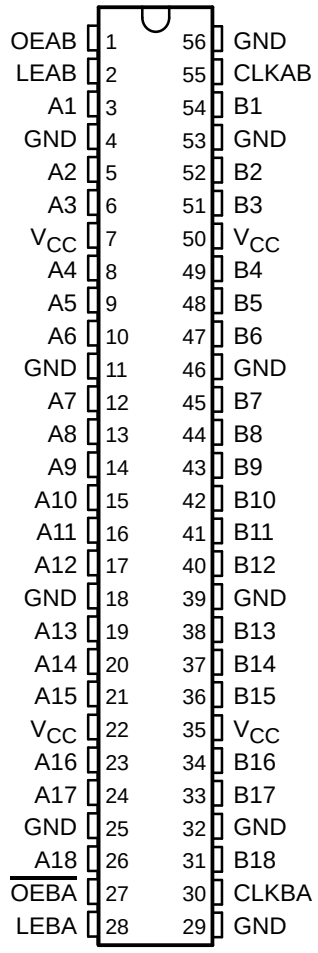
- **Members of the Texas Instruments *Widebus*™ Family**
- **B-Port Outputs Have Equivalent 25-Ω Series Resistors, So No External Resistors Are Required**
- **State-of-the-Art *EPIC*-II*B*™ BiCMOS Design Significantly Reduces Power Dissipation**
- ***UBT*™ (Universal Bus Transceiver) Combines D-Type Latches and D-Type Flip-Flops for Operation in Transparent, Latched, or Clocked Mode**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 500 mA Per JEDEC Standard JESD-17**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 5 V, T_A = 25°C**
- **High-Impedance State During Power Up and Power Down**
- **Flow-Through Architecture Optimizes PCB Layout**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages and 380-mil Fine-Pitch Ceramic Flat (WD) Package Using 25-mil Center-to-Center Spacings**

SN54ABT162501 . . . WD PACKAGE
SN74ABT162501 . . . DGG OR DL PACKAGE
(TOP VIEW)



description

These 18-bit universal bus transceivers consist of storage elements that can operate either as D-type latches or D-type flip-flops to allow data flow in transparent or clocked modes.

Data flow in each direction is controlled by output-enable (OEAB and $\overline{\text{OEBA}}$), latch-enable (LEAB and LEBA), and clock (CLKAB and CLKBA) inputs. For A-to-B data flow, the device operates in the transparent mode when LEAB is high. When LEAB is low, the A data is latched if CLKAB is held at a high or low logic level. If LEAB is low, the A data is stored in the latch/flip-flop on the low-to-high transition of CLKAB. When OEAB is high, the outputs are active. When OEAB is low, the outputs are in the high-impedance state.

Data flow for B to A is similar to that of A to B but uses $\overline{\text{OEBA}}$, LEBA, and CLKBA. The output enables are complementary (OEAB is active high and $\overline{\text{OEBA}}$ is active low).

The B-port outputs, which are designed to source or sink up to 12 mA, include equivalent 25-Ω series resistors to reduce overshoot and undershoot.

description (continued)

When V_{CC} is between 0 and 2.1 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 2.1 V, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor and OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.

The SN54ABT162501 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74ABT162501 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE†

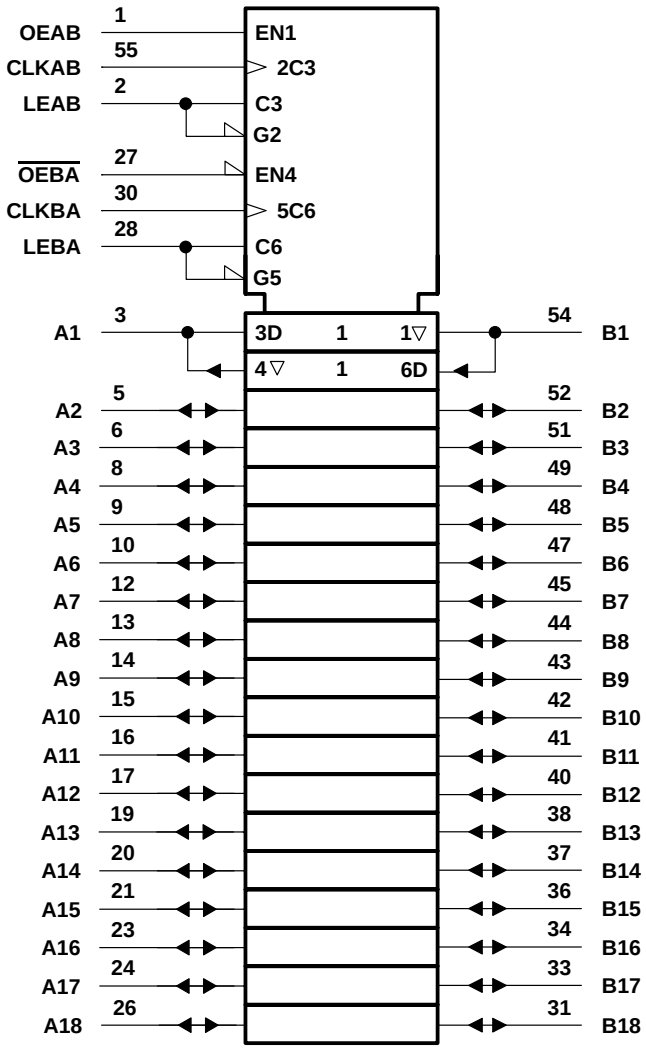
INPUTS				OUTPUT
OEAB	LEAB	CLKAB	A	B
L	X	X	X	Z
H	H	X	L	L
H	H	X	H	H
H	L	↑	L	L
H	L	↑	H	H
H	L	H	X	B_0‡
H	L	L	X	B_0§

† A-to-B data flow is shown: B-to-A flow is similar but uses $\overline{OEBA}$, LEBA, and CLKBA.

‡ Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low

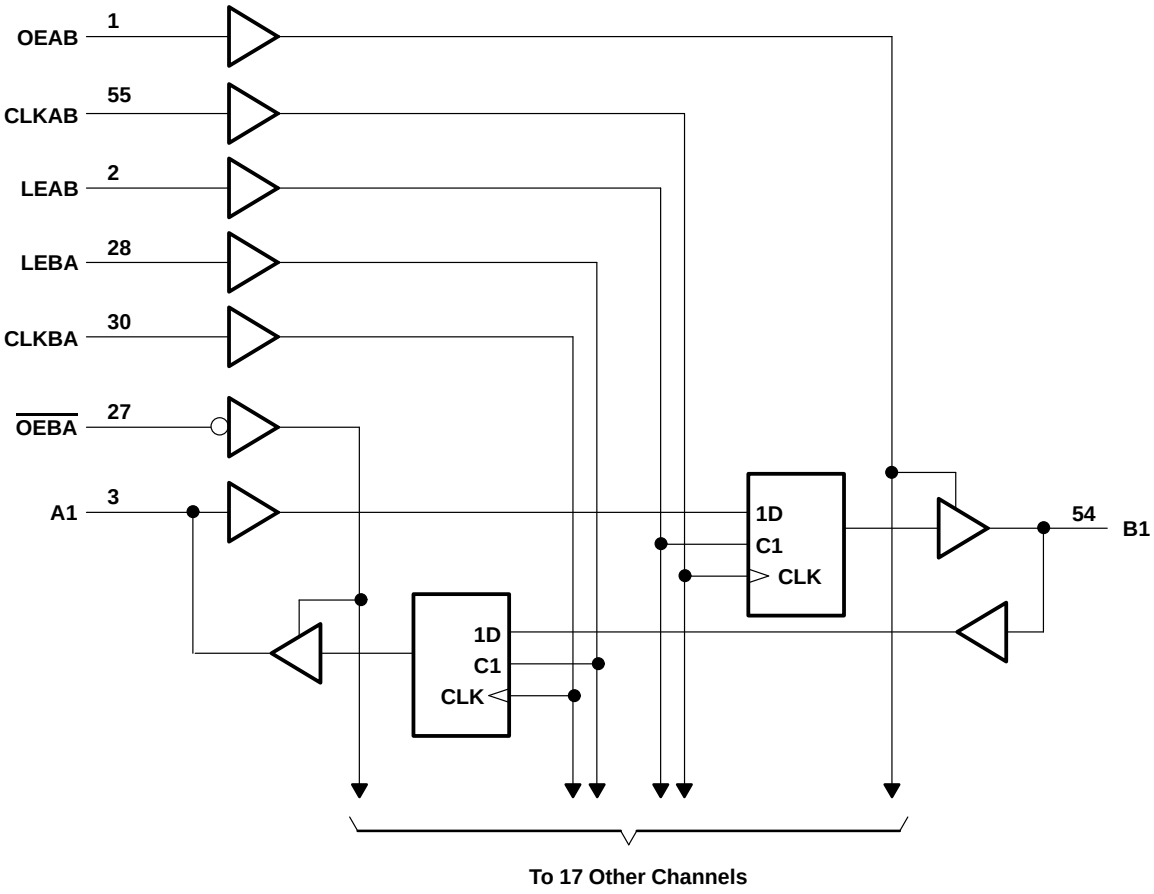
§ Output level before the indicated steady-state input conditions were established

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (except I/O ports) (see Note 1) . . . . . –0.5 V to 7 V
Voltage range applied to any output in the high or power-off state, V_O . . . . . –0.5 V to 5.5 V
Current into any output in the low state, I_O: SN54ABT162501 (A port) . . . . . 96 mA
SN74ABT162501 (A port) . . . . . 128 mA
B port . . . . . 30 mA
Input clamp current, I_{IK} (V_I < 0) . . . . . –18 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Package thermal impedance, θ_{JA} (see Note 2): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
2. The package thermal impedance is calculated in accordance with EIA/JEDEC Std JESD51.

recommended operating conditions (see Note 3)

			SN54ABT162501		SN74ABT162501		UNIT
			MIN	MAX	MIN	MAX	
V_{CC}	Supply voltage		4.5	5.5	4.5	5.5	V
V_{IH}	High-level input voltage		2		2		V
V_{IL}	Low-level input voltage			0.8		0.8	V
V_I	Input voltage		0	V_{CC}	0	V_{CC}	V
I_{OH}	High-level output current	A port		–24		–32	mA
		B port		–12		–12	
I_{OL}	Low-level output current	A port		48		64	mA
		B port		12		12	
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled		10		10	ns/V
$\Delta t/\Delta V_{CC}$	Power-up ramp rate		200		200		µs/V
T_A	Operating free-air temperature		–55	125	–40	85	°C

NOTE 3: Unused pins (input or I/O) must be held high or low to prevent them from floating.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A = 25°C			SN54ABT162501		SN74ABT162501		UNIT
				MIN	TYP†	MAX	MIN	MAX	MIN	MAX	
V_{IK}		V_{CC} = 4.5 V,	I_I = –18 mA			–1.2		–1.2		–1.2	V
V_{OH}	A port	V_{CC} = 4.5 V,	I_{OH} = –3 mA	2.5			2.5		2.5		V
		V_{CC} = 5 V,	I_{OH} = –3 mA	3			3		3		
		V_{CC} = 4.5 V	I_{OH} = –24 mA	2			2				
			I_{OH} = –32 mA	2*					2		
	B port	V_{CC} = 4.5 V,	I_{OH} = –1 mA	3.35			3.3		3.35		
		V_{CC} = 5 V,	I_{OH} = –1 mA	3.85			3.8		3.85		
		V_{CC} = 4.5 V	I_{OH} = –3 mA	3.1			3		3.1		
			I_{OH} = –12 mA	2.6					2.6		
V_{OL}	A port	V_{CC} = 4.5 V	I_{OL} = 48 mA			0.55		0.55			V
			I_{OL} = 64 mA			0.55*				0.55	
	B port	V_{CC} = 4.5 V,	I_{OL} = 12 mA			0.8		0.8		0.8	
V_{hys}					100						mV
I_I	Control inputs	V_{CC} = 0 to 5.5 V, V_I = V_{CC} or GND				±1		±1		±1	µA
	A or B ports	V_{CC} = 2.1 V to 5.5 V, V_I = V_{CC} or GND				±20		±20		±20	
I_{OZPU}‡		V_{CC} = 0 to 2.1 V, V_O = 0.5 V to 2.7 V, $\overline{OE}$ or OE = X				±50		±50		±50	µA
I_{OZPD}‡		V_{CC} = 2.1 V to 0, V_O = 0.5 V to 2.7 V, $\overline{OE}$ or OE = X				±50		±50		±50	µA
I_{OZH}§		V_{CC} = 2.1 V to 5.5 V, V_O = 2.7 V, $\overline{OE}$ ≥ 2 V or OE ≤ 0.8 V¶				10		10		10	µA
I_{OZL}§		V_{CC} = 2.1 V to 5.5 V, V_O = 0.5 V, $\overline{OE}$ ≥ 2 V or OE ≤ 0.8 V¶				–10		–10		–10	µA
I_{off}		V_{CC} = 0,	V_I or V_O ≤ 4.5 V			±100				±100	µA
I_{CEX}	Outputs high	V_{CC} = 5.5 V,	V_O = 5.5 V			50		50		50	µA
I_O#	A port	V_{CC} = 5.5 V,	V_O = 2.5 V	–50	–110	–180	–50	–180	–50	–180	mA
	B port	V_{CC} = 5.5 V,	V_O = 2.5 V	–25	–55	–90	–25	–90	–25	–90	
I_{CC}	A or B ports	V_{CC} = 5.5 V, I_O = 0, V_I = V_{CC} or GND	Outputs high			3		3		3	mA
			Outputs low			36		36		36	
			Outputs disabled			3		3		3	
ΔI_{CC}‖		V_{CC} = 5.5 V, One input at 3.4 V, Other inputs at V_{CC} or GND				50		50		50	µA
C_i	Control inputs	V_I = 2.5 V or 0.5 V			3						pF
C_{io}	A or B ports	V_O = 2.5 V or 0.5 V			9						pF

* On products compliant to MIL-PRF-38535, this parameter does not apply.
† All typical values are at V_{CC} = 5 V.
‡ This parameter is characterized, but not production tested.
§ The parameters I_{OZH} and I_{OZL} include the input leakage current.
¶ For V_{CC} between 2.1 V and 4 V, OE should be less than or equal to 0.5 V to ensure a low state.
# Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
‖ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

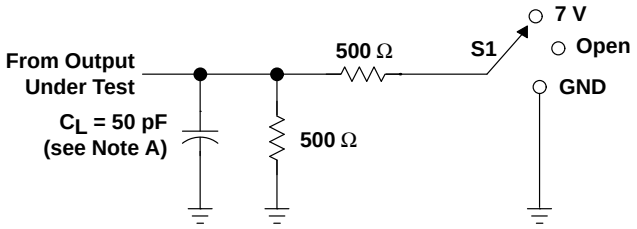
				SN54ABT162501		SN74ABT162501		UNIT
				MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency			0	150	0	150	MHz
t_w†	Pulse duration	LEAB or LEBA high		3		3		ns
		CLKAB or CLKBA high or low		3.3		3.3		
t_{su}	Setup time	A before CLKAB↑		4.3		4.3		ns
		B before CLKBA↑		4.3		4.3		
		A before LEAB↓ or B before LEBA↓	CLK high	2.5		2.5		
			CLK low	1		1		
t_h	Hold time	A after CLKAB↑ or B after CLKBA↑		0		0		ns
		A after LEAB↓ or B after LEBA↓		2		2		

† This parameter is characterized, but not production tested.

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, C_L = 50 pF (unless otherwise noted) (see Figure 1)

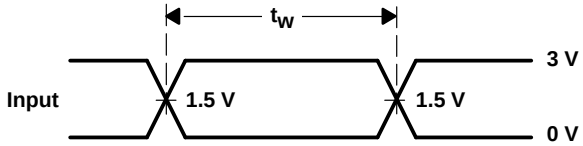
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 5 V, T_A = 25°C			SN54ABT162501		SN74ABT162501		UNIT
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	
f_{max}			150	200		150		150		MHz
t_{PLH}	A or B	B or A	1.5	2.6	4	1.5	5.1	1.5	4.8	ns
t_{PHL}			2	3.4	5.2	2	6.1	2	5.7	
t_{PLH}	LEAB or LEBA	B or A	2	3.3	4.8	2	6.1	2	5.6	ns
t_{PHL}			2	3.8	5.2	2	6.4	2	5.9	
t_{PLH}	CLKAB or CLKBA	B or A	1.5	3.5	4.7	1.5	6	1.5	5.5	ns
t_{PHL}			1.5	3.5	4.8	1.5	5.8	1.5	5.3	
t_{PZH}	OEAB or $\overline{OEBA}$	B or A	1.5	3.4	4.6	1.5	5.6	1.5	5.3	ns
t_{PZL}			2	3.8	4.7	2	5.6	2	5.4	
t_{PHZ}	OEAB or $\overline{OEBA}$	B or A	2	4.5	5.7	2	6.9	2	6.5	ns
t_{PLZ}			1.5	3.8	5.3	1.5	6.3	1.5	5.8	

PARAMETER MEASUREMENT INFORMATION

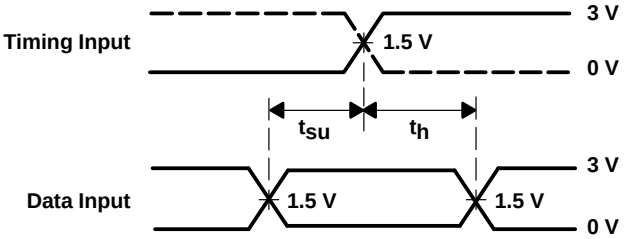


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open

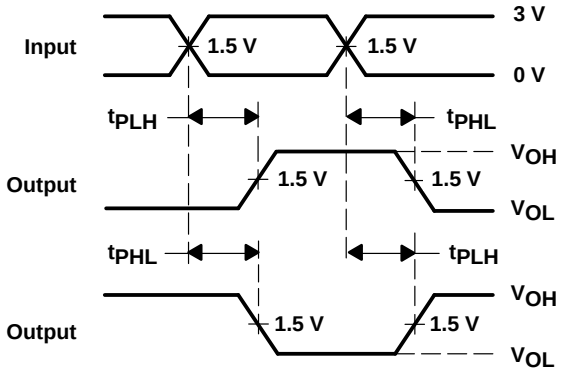
LOAD CIRCUIT



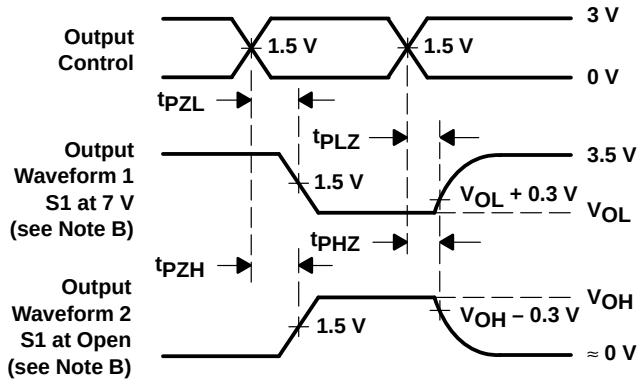
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

IMPORTANT NOTICE

Texas Instruments (TI) reserves the right to make changes to its products or to discontinue any semiconductor product or service without notice, and advises its customers to obtain the latest version of relevant information to verify, before placing orders, that the information being relied on is current.

TI warrants performance of its semiconductor products and related software to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Certain applications using semiconductor products may involve potential risks of death, personal injury, or severe property or environmental damage ("Critical Applications").

TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, INTENDED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT APPLICATIONS, DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS.

Inclusion of TI products in such applications is understood to be fully at the risk of the customer. Use of TI products in such applications requires the written approval of an appropriate TI officer. Questions concerning potential risk applications should be directed to TI through a local SC sales office.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards should be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance, customer product design, software performance, or infringement of patents or services described herein. Nor does TI warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used.